

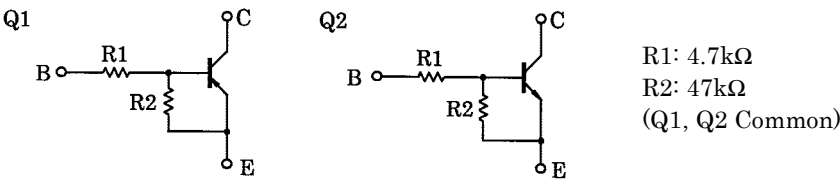
TOSHIBA Transistor
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

RN4906

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values



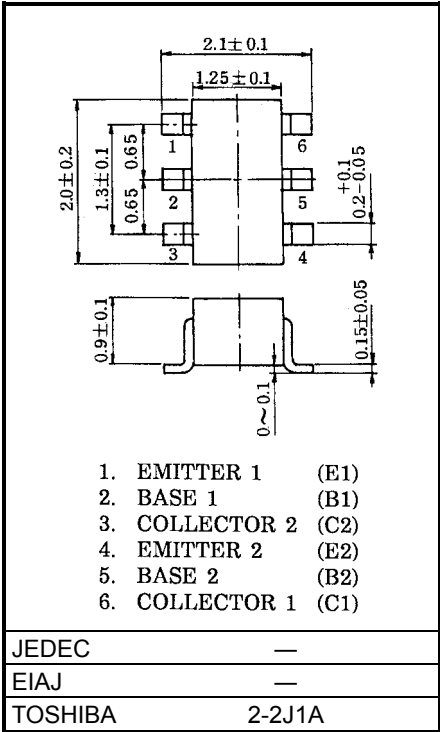
Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA

Unit: mm



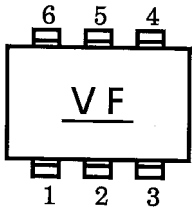
Weight: 6.8mg

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

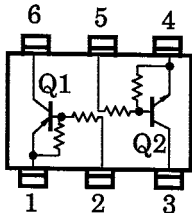
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P_C *	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

* Total rating

Marking



Equivalent Circuit (Top View)



Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	—	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
	I_{CEO}	—	$V_{CE} = -50V, I_B = 0$	—	—	-500	
Emitter cut-off current	I_{EBO}	—	$V_{EB} = -5V, I_C = 0$	-0.074	—	-0.138	mA
DC current gain	h_{FE}	—	$V_{CE} = -5V, I_C = -10mA$	80	—	—	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Input voltage (ON)	$V_I(ON)$	—	$V_{CE} = -0.2V, I_C = -5mA$	-0.7	—	-1.3	V
Input voltage (OFF)	$V_I(OFF)$	—	$V_{CE} = -5V, I_C = -0.1mA$	-0.5	—	-0.8	V
Transition frequency	f_T	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector output capacitance	C_{ob}	—	$V_{CB} = -10V, I_E = 0$	—	3	6	pF